# **Octal Bus Transceiver**

# With 5 V-Tolerant Inputs

The MC74LVX245 is an advanced high speed CMOS octal bus transceiver.

It is intended for two-way asynchronous communication between data buses. The direction of data transmission is determined by the level of the  $T/\overline{R}$  input. The output enable pin  $(\overline{OE})$  can be used to disable the device, so that the buses are effectively isolated.

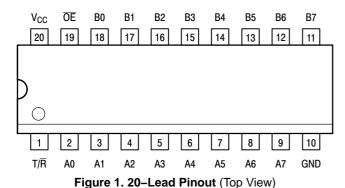
All inputs are equipped with protection circuits against static discharge.

#### **Features**

- High Speed:  $t_{PD} = 4.7 \text{ ns (Typ)}$  at  $V_{CC} = 3.3 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 4 \mu A$  (Max) at  $T_A = 25$ °C
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Low Noise:  $V_{OLP} = 0.8 \text{ V (Max)}$
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: Human Body Model > 2000 V; Machine Model > 200 V
- Pb-Free Packages are Available

#### **Application Notes**

- Do not force a signal on an I/O pin when it is an active output, damage may occur
- All floating (high impedance) input or I/O pins must be fixed by means of pullup or pulldown resistors or bus terminator ICs
- A parasitic diode is formed between the bus and V<sub>CC</sub> terminals.
   Therefore, the LVX245 cannot be used to interface 5.0 V to 3.0 V systems directly

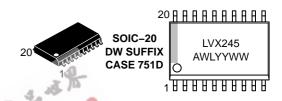


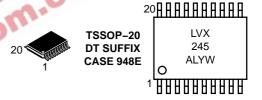
<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

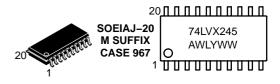


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#### MARKING DIAGRAMS



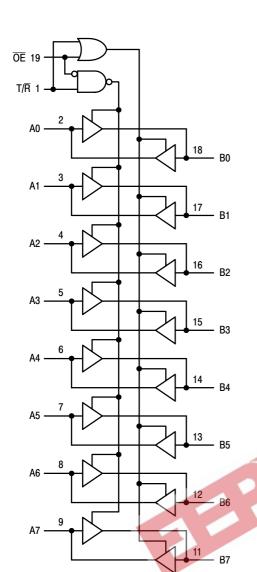




A = Assembly Location
WL, L = Wafer Lot
Y, YY = Year
W. WW = Work Week

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.



**Table 1. PIN NAMES** 

I som.cn

Pins	Function
OE	Output Enable Input
T/R	Transmit/Receive Input
A0–A7	Side A 3-State Inputs or 3-State Outputs
Bo–B7	Side B 3-State Inputs or 3-State Outputs

INP	JTS	OPERATING MODE
OE	T/R	Non-Inverting
L	L	B Data to A Bus
L	Н	A Data to B Bus
Н	Х	Z

H = High Voltage Level; L = Low Voltage Level; Z = High Impedance State; X = High or Low Voltage Level and Transitions are Acceptable; For I<sub>CC</sub> reasons, Do Not Float Inputs



## **ORDERING INFORMATION**

Device	Package	Shipping $^{\dagger}$
MC74LVX245DWR2	SOIC-20	1000 / Tape & Reel
MC74LVX245DWR2G	SOIC-20 (Pb-Free)	1000 / Tape & Reel
MC74LVX245DTR2	TSSOP-20*	2500 / Tape & Reel
MC74LVX245M	SOEIAJ-20 (Pb-Free)	50 Units / Rail
MC74LVX245MEL	SOEIAJ-20 (Pb-Free)	2000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>This package is inherently Pb-Free.

## **MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage	-0.5 to +7.0	V
V <sub>in</sub>	DC Input Voltage (T/R, OE)	-0.5 to +7.0	V
V <sub>I/O</sub>	DC Output Voltage	$-0.5$ to $V_{CC}$ +0.5	٧
I <sub>IK</sub>	Input Diode Current	-20	mA
I <sub>OK</sub>	Output Diode Current	±20	mA
l <sub>out</sub>	DC Output Current, per Pin	±25	mA
Icc	DC Supply Current, V <sub>CC</sub> and GND Pins	±75	mA
P <sub>D</sub>	Power Dissipation	180	mW
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

## **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage	2.0	3.6	V
V <sub>in</sub>	DC Input Voltage (T/R, OE)	0	5.5	V
V <sub>I/O</sub>	DC Output Voltage	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature, All Package Types	-40	+85	°C
Δt/ΔV	Input Rise and Fall Time	0	100	ns/V

	CTRICAL CHARACTERISTICS		Ι.,	Т	T <sub>A</sub> = 25°C		T <sub>A</sub> = - 40 to 85°C		
Symbol	Parame <mark>ter</mark>	Test Conditions	v <sub>cc</sub>	Min	Тур	Max	Min	Max	Unit
V <sub>IH</sub>	High-Level Input Voltage		2.0 3.0 3.6	1.5 2.0 2.4			1.5 2.0 2.4		V
V <sub>IL</sub>	Low-Level Input Voltage		2.0 3.0 3.6			0.5 0.8 0.8		0.5 0.8 0.8	V
V <sub>OH</sub>	High-Level Output Voltage (V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub> )	$I_{OH} = -50 \mu A$ $I_{OH} = -50 \mu A$ $I_{OH} = -4 \text{ mA}$	2.0 3.0 3.0	1.9 2.9 2.58	2.0 3.0		1.9 2.9 2.48		V
V <sub>OL</sub>	Low-Level Output Voltage (V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub> )	I <sub>OL</sub> = 50 μA I <sub>OL</sub> = 50 μA I <sub>OL</sub> = 4 mA	2.0 3.0 3.0		0.0 0.0	0.1 0.1 0.36		0.1 0.1 0.44	V
I <sub>in</sub>	Input Leakage Current	$V_{in} = 5.5 \text{ V or GND}$ (T/R, $\overline{\text{OE}}$ )	3.6			±0.1		±1.0	μΑ
l <sub>OZ</sub>	Maximum 3–State Leakage Current	$V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or GND}$	3.6			±0.2 5		±2.5	μΑ
I <sub>CC</sub>	Quiescent Supply Current	V <sub>in</sub> = V <sub>CC</sub> or GND	3.6			4.0		40.0	μΑ

## AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$ )

				Т	A = 25°	С	$T_A = -40$	to 85°C	
Symbol	Parameter	Test Cond	ditions	Min	Тур	Max	Min	Max	Unit
t <sub>PLH</sub> ,	Propagation Delay Input to Output	V <sub>CC</sub> = 2.7 V	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		6.1 8.6	10.7 14.2	1.0 1.0	13.5 17.0	ns
		$V_{CC} = 3.3 \pm 0.3 \text{ V}$	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		4.7 7.2	6.6 10.1	1.0 1.0	8.0 11.5	
t <sub>PZL</sub> , t <sub>PZH</sub>	Output Enable Time to High and Low Level	$V_{CC} = 2.7 \text{ V}$ $R_L = 1 \text{ k}\Omega$	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		9.0 11.5	16.9 20.4	1.0 1.0	20.5 24.0	ns
		$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $R_L = 1 \text{ k}\Omega$	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		7.1 9.6	11.0 14.5	1.0 1.0	13.0 16.5	
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Output Disable Time From High and Low Level	$V_{CC} = 2.7 \text{ V}$ $R_L = 1 \text{ k}\Omega$	C <sub>L</sub> = 50 pF		11.5	18.0	1.0	21.0	ns
		$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $R_L = 1 \text{ k}\Omega$	C <sub>L</sub> = 50 pF		9.6	12.8	1.0	14.5	
t <sub>OSHL</sub>	Output-to-Output Skew (Note 1)	V <sub>CC</sub> = 2.7 V V <sub>CC</sub> = 3.3 ±0.3 V	$C_L = 50 \text{ pF}$ $C_L = 50 \text{ pF}$			1.5 1.5		1.5 1.5	ns

Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device.

The specification applies to any outputs switching in the same direction, either HIGH—to—LOW (toshl) or LOW—to—HIGH (toslh); parameter guaranteed by design.

CAPACITIVE CHARACTERISTICS

		132	Ţ	<sub>A</sub> = 25°	С	$T_A = -40$	to 85°C	
Symbol	Parameter	C	Min	Тур	Max	Min	Max	Unit
C <sub>in</sub>	Input Capacitance (T/R, OE)			4	10		10	pF
C <sub>I/O</sub>	Maximum 3–State I/O Capacitance			8				pF
C <sub>PD</sub>	Power Dissipation Capacitance (Note 2)			21				pF

 $C_{PD}$  is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation:  $I_{CC(OPR)} = C_{PD} \cdot V_{CC} \cdot f_{in} + I_{CC}/8$  (per bit).  $C_{PD}$  is used to determine the no–load dynamic power consumption;  $P_D = C_{PD} \cdot V_{CC}^2 \cdot f_{in} + I_{CC} \cdot V_{CC}$ .

## **NOISE CHARACTERISTICS** (Input $t_r = t_f = 3.0$ ns, $C_L = 50$ pF, $V_{CC} = 3.3$ V, Measured in SOIC Package)

			T <sub>A</sub> = 25°C		
Symbol	Characteristic	Тур	Max	Unit	
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>	0.5	0.8	V	
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>	-0.5	-0.8	V	
V <sub>IHD</sub>	Minimum High Level Dynamic Input Voltage		2.0	V	
V <sub>ILD</sub>	Maximum Low Level Dynamic Input Voltage		0.8	V	

## **SWITCHING WAVEFORMS**

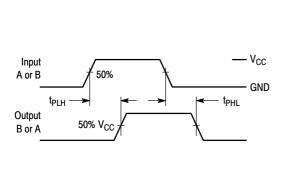


Figure 3.

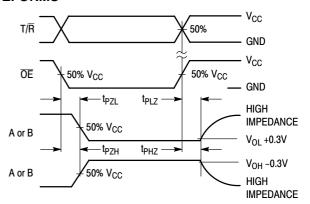
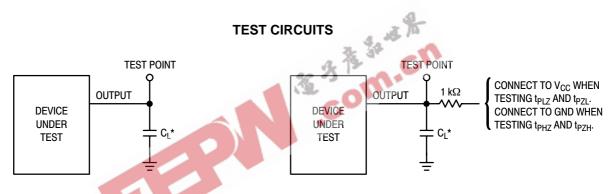


Figure 4.



\*Includes all probe and jig capacitance

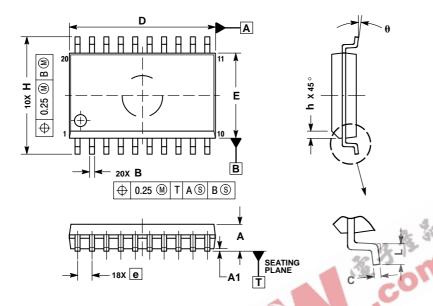
\*Includes all probe and jig capacitance

Figure 5. Propagation Delay Test Circuit

Figure 6. 3-State Test Circuit

#### PACKAGE DIMENSIONS

### SOIC-20 **DW SUFFIX** CASE 751D-05 ISSUE G



#### **NOTES**

- DIMENSIONS ARE IN MILLIMETERS.
  INTERPRET DIMENSIONS AND TOLERANCES
  PER ASME Y14.5M, 1994.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD
- PROTRUSION
- PROTRUSION.

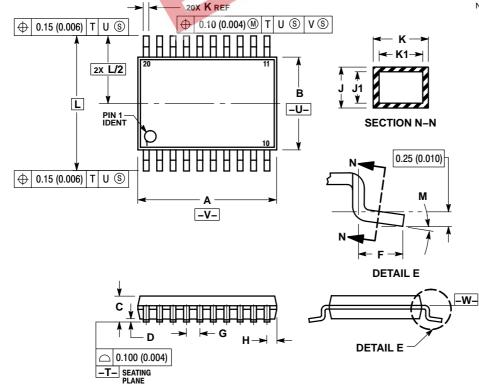
  MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

  DIMENSION B DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABLE PROTRUSION
  SHALL BE 0.13 TOTAL IN EXCESS OF B

  DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS				
DIM	MIN	MAX			
Α	2.35	2.65			
A1	0.10	0.25			
В	0.35	0.49			
С	0.23	0.32			
D	12.65	12.95			
E.	7.40	7.60			
е	1.27	BSC			
Н	10.05	10.55			
h	0.25	0.75			
L	0.50	0.90			
θ	0 °	7 °			

TSSOP-20 **DT SUFFIX** CASE 948E-02 **ISSUE B** 



#### NOTES:

- DIES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

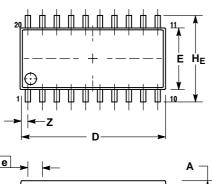
  2. CONTROLLING DIMENSION:
  MILLIMETER.

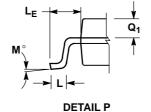
- MILLIME I ER.
  3. DIMENSION A DOES NOT INCLUDE
  MOLD FLASH, PROTRUSIONS OR GATE
  BURRS. MOLD FLASH OR GATE BURRS
  SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- SIDE.
  5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
  6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
  7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

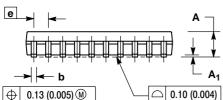
	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	6.40	6.60	0.252	0.260	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.27	0.37	0.011	0.015	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40	6.40 BSC		BSC	
M	0°	8°	0°	8°	

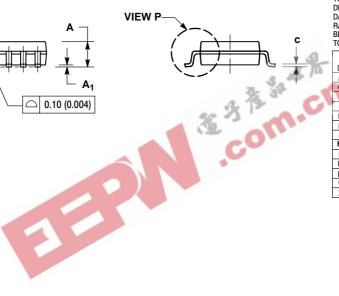
#### PACKAGE DIMENSIONS

## SOEIAJ-20 **M SUFFIX** CASE 967-01 **ISSUE O**









- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI
  Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. STAFFICIONS D AND E DO NOT INCLUDE MOLD 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR
- AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

  TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
  THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MAX	
Α		2.05		0.081
A <sub>1</sub>	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.18	0.27	0.007	0.011
D	12.35	12.80	0.486	0.504
Е	5.10	5.45	0.201	0.215
е	1.27	BSC	0.050	BSC
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10°	0 °	10 °
Q <sub>1</sub>	0.70	0.90	0.028	0.035
Z		0.81		0.032



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